

Abstract of the Disclosure

A semiconductor device having a ferroelectric capacitor is provided. The semiconductor device includes an interlayer insulating layer, a ferroelectric capacitor and an insulating side wall film. The interlayer insulating layer is formed on a substrate including an integrated circuit and has a contact hole exposing a part of the integrated circuit. The ferroelectric capacitor is formed by depositing a first electrode layer, a ferroelectric layer and a second electrode layer on the interlayer insulating layer in this order. The insulating side wall film covers a peripheral edge section of the ferroelectric capacitor and is spaced from a peripheral edge section of the contact hole. A wiring layer electrically connects the second electrode layer to the integrated circuit through the contact hole.